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## **S602ECS**





## **Main Features**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	1.5	А
V <sub>DRM</sub> /V <sub>RRM</sub>	600	V
I <sub>GT</sub>	100	μА

## **Applications**

The S602ECS is specifically designed for Gas Ignition applications that require high pulse surge current capability.

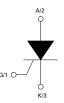
## Description

This new .8 A sensitive gate SCR in an TO-92 package with a GAK pin out, offers a high static component series with a high static dv/dt and a low turn off  $(t_q)$  time by the use of small die planar construction implementation. All SCR's junctions are glass-passivated to ensure long term reliability and parametric stability.

#### **Features**

- Surge capability >15Amps
- High dv/dt noise immunity
- Improved turn-off time (t<sub>q</sub>) ≤ 35 µs
- TO-92 G-A-K pinout
- Sensitive gate for direct microprocessor interface
- RoHS compliant and Halogen-Free

## **Schematic Symbol**



## **Absolute Maximum Ratings**

Symbol	Parameter			Value	Unit
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave)	1 - 65°		1.5	А
I <sub>T(AV)</sub>	Average on-state current	T <sub>c</sub> =	65°C	0.95	А
	Non repetitive surge peak on-state cu	rrent	F = 50 Hz	14.0	
I <sub>TSM</sub>	(Single cycle, T <sub>J</sub> initial = 25°C)		F = 60 Hz	16.8	A
l²t	12+ Value for funing	t <sub>p</sub> = 10 ms	F = 50 Hz	0.78	A²s
I-t	l <sup>2</sup> t Value for fusing	$t_p = 8.3 \text{ ms}$	F = 60 Hz	0.93	A-5
di/dt	Critical rate of rise of on-state current IG	= 10mA	T <sub>J</sub> = 125°C	50	A/µs
I <sub>GM</sub>	Peak gate current $t_p = 10 \ \mu s$ $T_J = 125$		T <sub>J</sub> = 125°C	1.0	А
$P_{G(AV)}$	Average gate power dissipation $T_J = 125$ °C			0.1	W
T <sub>stg</sub>	Storage junction temperature range			-40 to 150	°C
T	Operating junction temperature range			-40 to 125	°C



## Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified)

Cumphal	Description	Test Conditions	S602ECS		Unit
Symbol	Description	lest Conditions	Min	Max	Onit
I <sub>GT</sub>	DC Gate Trigger Current	V <sub>D</sub> = 12V	20	100	μΑ
V <sub>GT</sub>	DC Gate Trigger Voltage	$R_L = 60 \Omega$	_	0.8	V
$V_{GRM}$	Peak Reverse Gate Voltage	$I_{RG} = 10\mu A$	5	_	V
I <sub>H</sub>	Holding Current	$R_{GK} = 1 k\Omega$	_	3	mA
(dv/dt)s	Critical Rate-of-Rise of Off-State Voltage	$T_{J} = 125^{\circ}\text{C}$ $V_{D} = V_{DRM} / V_{RRM}$ Exponential Waveform $R_{GK} = 1 \text{ k}\Omega$	50	_	V/µs
t <sub>q</sub>	Turn-Off Time	$T_J = 125^{\circ}C @ 600 V$ $R_{GK} = 1 k\Omega$	_	35	μs
t <sub>gt</sub>	Turn-On Time	$I_{\rm G} = 10$ mA PW = 15 $\mu$ sec $I_{\rm T} = 3.0$ A (pk)	_	3	μs

## Static Characteristics (T<sub>j</sub> = 25°C, unless otherwise specified)

Symbol	Symbol Description Test Conditions		Value		Unit
Syllibol	Description	lest Conditions	Min	Max	Offit
V <sub>TM</sub>	Peak On-State Voltage	I <sub>TM</sub> = 4A (pk)	_	1.8	V
Off Casts County Deal Deposition	$T_J = 25^{\circ}\text{C} @ V_D = V_{DRM}$ $R_{GK} = 1 \text{ k}\Omega$	_	5	μΑ	
I <sub>DRM</sub>	I <sub>DRM</sub> Off-State Current, Peak Repetitive	$T_J = 125^{\circ}C @V_D = V_{DRM}$ $R_{GK} = 1 k\Omega$	_	500	μΑ

## **Thermal Resistances**

Symbol	Parameter		Value	Unit
R <sub>e(J-C)</sub>	Junction to case (AC)	I <sub>T</sub> = 1.5A <sub>(RMS)</sub> , 60Hz AC resistive load condition, 100% conduction.	50	°C/W
R <sub>e(J-A)</sub>	Junction to ambient	condition, 100% conduction.	160	°C/W

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

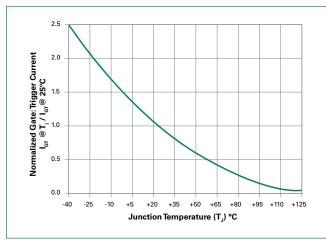


Figure 2: Normalized DC Holding Current vs. Junction Temperature

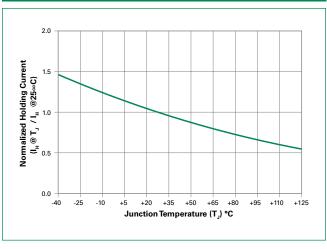




Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature

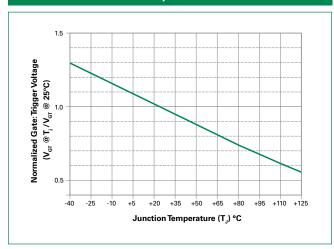


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

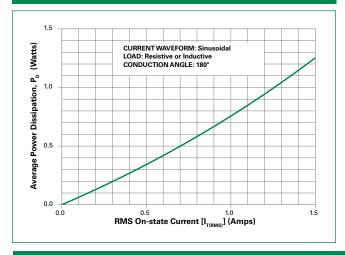


Figure 4: On-State Current vs. On-State Voltage (Typical)

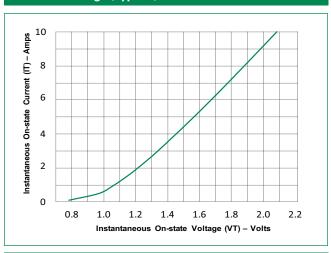


Figure 6: Maximum Allowable Case Temperature vs. On-State Current

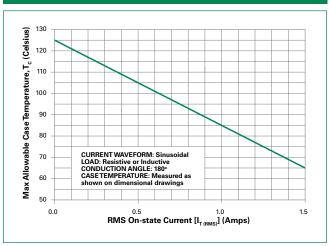
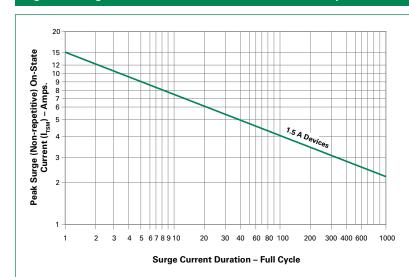


Figure 6: Surge Peak On-State Current vs. Number of Cycles



Supply Frequency: 60Hz Sinusoidal

RMS On-State Current  $[I_{T(RMS)}]$ : Max Rated Value at Specific Case Temperature

Notes:

 Gate control may be lost during and immediately following surge current interval.

2. Overload may not be repeated until junction temperature has returned to steady-state rated value.



Figure 7: Typical DC Gate Trigger Current with RGK vs. Junction Temperature

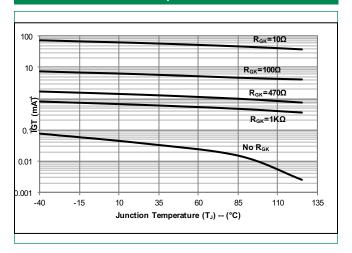


Figure 8: Typical DC Holding Current with RGK vs. Junction Temperature

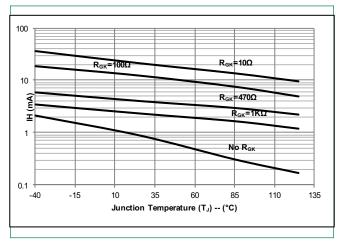


Figure 9: Typical Turn Off Time with RGK vs. Junction Temperature

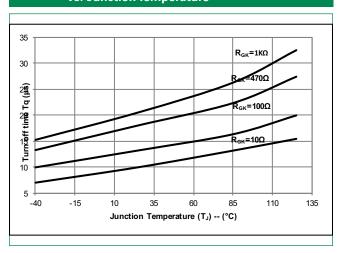
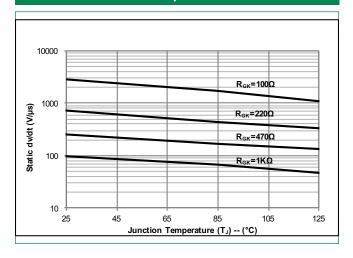


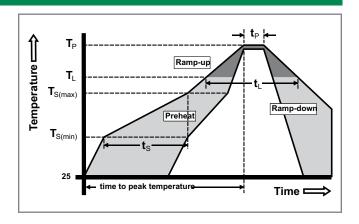
Figure 10: Typical Static DV/DT with RGK vs. Junction Temperature





## **Soldering Parameters**

Reflow Condition		Pb – Free assembly	
	-Temperature Min (T <sub>s(min)</sub> )	150°C	
Pre Heat	-Temperature Max (T <sub>s(max)</sub> )	200°C	
	-Time (min to max) (t <sub>s</sub> )	60 – 180 secs	
Average ramp up rate (Liquidus Temp) (T <sub>L</sub> ) to peak		5°C/second max	
T <sub>S(max)</sub> to T <sub>l</sub>	- Ramp-up Rate	5°C/second max	
Reflow	-Temperature (T <sub>L</sub> ) (Liquidus)	217°C	
nellow	-Time (min to max) (t <sub>s</sub> )	60 – 150 seconds	
PeakTemp	perature (T <sub>P</sub> )	260 <sup>+0/-5</sup> °C	
Time within 5°C of actual peak Temperature (t <sub>p</sub> )		20 - 40 seconds	
Ramp-down Rate		5°C/second max	
Time 25°C to peak Temperature (T <sub>P</sub> )		8 minutes Max.	
Do not exceed		280°C	



## **Physical Specifications**

Terminal Finish	100% Matte Tin-plated.
Body Material	UL Recognized epoxy meeting flammability rating V-0.
Lead Material	Copper Alloy

#### **Design Considerations**

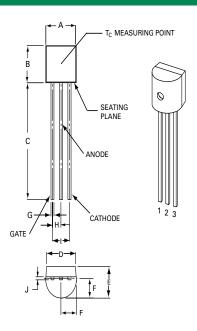
Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

## **Environmental Specifications**

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/ Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E



## **Dimensions**

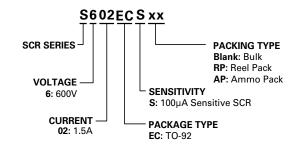


Dimensions	Inches		Millimeters	
Difficusions	Min	Max	Min	Max
А	0.175	0.205	4.450	5.200
В	0.170	0.210	4.320	5.330
С	0.500	_	12.700	_
D	0.135	_	3.430	_
Е	0.125	0.165	3.180	4.190
F	0.080	0.105	2.040	2.660
G	0.016	0.021	0.407	0.533
Н	0.045	0.055	1.150	1.390
I	0.095	0.105	2.420	2.660
J	0.015	0.020	0.380	0.500

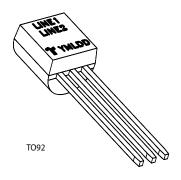
## **Packing Options**

Part Number	Marking	Weight	Packing Mode	Base Quantity
S602ECS	S602ECS	0.170 g	Bulk	2500
S602ECSAP	S602ECS	0.170 g	Ammo Pack	2000
S602ECSRP	S602ECS	0.170 g	Tape & Reel	2000

## **Part Numbering System**



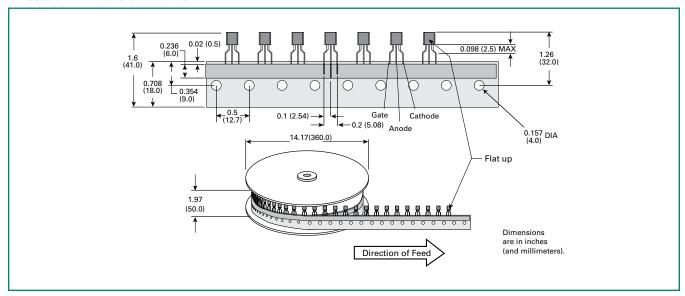
## **Part Marking System**





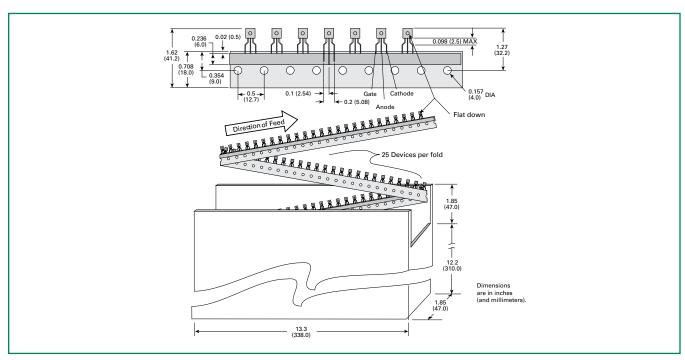
## TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

#### Meets all EIA-468-C Standards



## TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

#### Meets all EIA-468-C Standards



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